
SPECIFICATION

ITEM	WHITE SIDE VIEW LED
MODEL	SWAF3L
CUSTOMER	

Customer

Approved by	Approved by	Approved by
/	/	/

Supplier

Drawn by	Checked by	Approved by
/	/	/



SEOUL SEMICONDUCTOR CO., LTD.

Contents

1. Features	02
2. Application	02
3. Absolute Maximum Ratings	03
4. Electro-Optical Characteristics	03
5. CIE Chromaticity Diagram	04
6. Characteristic Diagram	05
7. Reliability	08
8. Precautions	09
9. Soldering Profile	10
10. Outline Dimension	11
11. History	12

1. Features

- Package: SMT Solderability
- Dimension : 7.0 × 2.0 × 1.9 (mm)
- Low Thermal Resistance
- RoHS Compliant, Lead Free
- 6-Pin (Blue separate) type
- Own Patent Reserved
- SWAF3L is Very Useful Side View LED in Back Light Unit Application

2. Applications

- Flat Backlighting (LCD, Display)
- Camera, PDA, CNS, Notebook
- Coupling into Light Guide Panel
- Illuminations

3. Absolute Maximum Ratings

 $(T_a = 25^\circ\text{C})$

Parameter	Symbol	Value	Unit
Power Dissipation	P_d^{*1}	280	mW
Forward Current	I_F	80	mA
Peak Forward Current	I_{FM}^{*2}	200	mA
Reverse Voltage	V_R	5	V
Operating Temperature	T_{opr}	-30 ~ +85	$^\circ\text{C}$
Storage Temperature	T_{stg}	-40 ~ +100	$^\circ\text{C}$
Thermal Resistance (junction to solder)	$R\theta_{j-s}$	70	$^\circ\text{C}/\text{W}$
Junction Temperature	$T_{j\ max}$	125	$^\circ\text{C}$

*1 Care is to be taken that Power Dissipation does not exceed the Absolute Maximum Rating of the product.

*2 I_{FM} conditions : Pulse width $T_W \leq 0.1\text{ms}$, Duty ratio $\leq 1/10$

4. Electro-Optical Characteristics

 $(T_a = 25^\circ\text{C})$

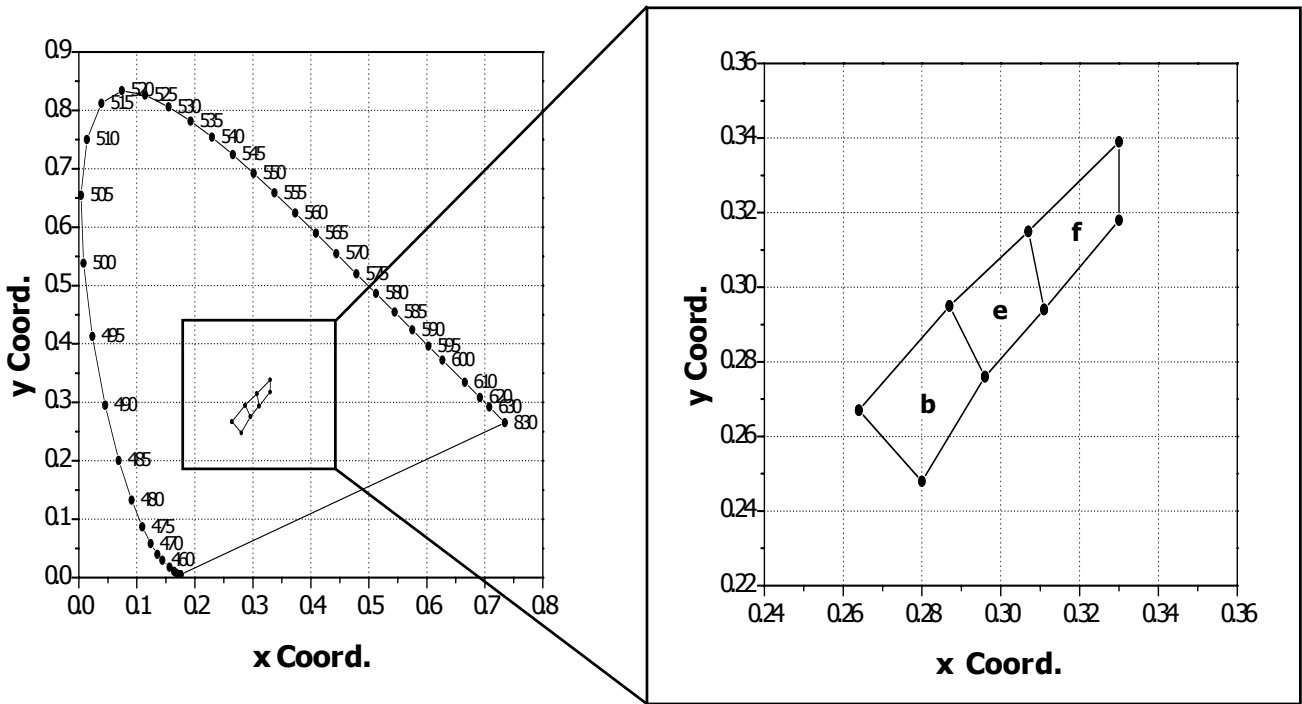
Item	Symbol	Condition	Min	Typ	Max	Unit	
Forward Voltage	V_F	$I_F = 20\ \text{mA}/\text{CHIP}$	2.9	3.2	3.6	V	
Reverse Current	I_R	$V_R = 5\ \text{V}$	-	-	100	μA	
Thermal Resistance(Junction to solder)	$R\theta_{j-s}$	$I_F = 20\ \text{mA}/\text{CHIP}$	70			$^\circ\text{C}/\text{W}$	
Luminous Intensity ^{*1}	Rank M1	I_V	$I_F = 60\ \text{mA}$	4100	-	4400	mcd
	Rank M4			4400	-	4700	
	Rank M7			4700	-	5000	
	Rank N0			5000	-	5300	
	Rank N3			5300	-	5600	
Viewing Angle ^{*2}	$2\theta_{1/2}$	$I_F = 60\ \text{mA}$	120			$^\circ$	
Color Coordinates ^{*3}	Rank b	x	$I_F = 60\ \text{mA}$	0.264	-	0.296	-
		y		0.248	-	0.295	
	Rank e	x		0.287	-	0.311	
		y		0.276	-	0.315	
	Rank f	x		0.307	-	0.330	
		y		0.294	-	0.339	
Life Time ^{*4}	$T_a = 25^\circ\text{C}, I_F = 20\ \text{mA}/\text{CHIP}$		15000 hrs			-	

*1 The luminous intensity I_V is measured at the peak of the spatial pattern which may not be aligned with the mechanical axis of the LED package. Luminous Intensity Measurement allowance is $\pm 10\%$.*2 $\theta_{1/2}$ is the off-axis where the luminous intensity is 1/2 of the peak intensity.*3 Measurement Uncertainty of the Color Coordinates is ± 0.01

*4 Estimated time to 50% degradation of initial luminous intensity.(A chip = 20mA)

* Note : All products confirm to the listed minimum and maximum specifications for electric and optical characteristics, when operated at 20mA within the maximum ratings shown above. All measurements were made under the standardized environment of Seoul Semiconductor.

5. CIE Chromaticity Diagram



● Luminous Intensity

Ranking by Color Coordinates				b	e	f
Ranking by Luminous Intensity						
RANK	Min	Max	Unit			
M1	4100	4400	mcd	√	√	
M4	4400	4700		√	√	
M7	4700	5000		√	√	√
N0	5000	5300			√	√
N3	5300	5600			√	√

● The Checked ranks are available

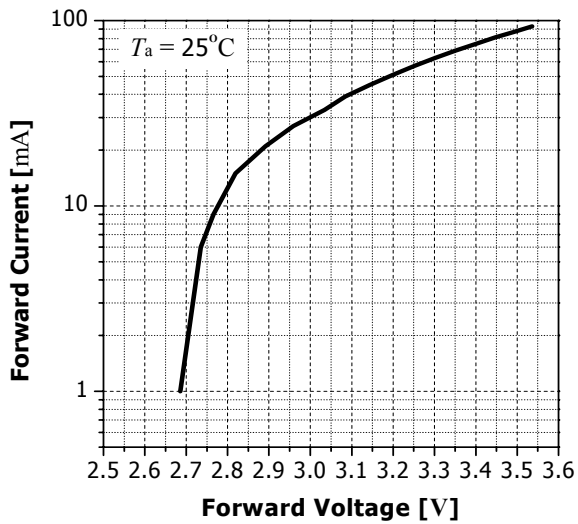
● Color Rank

($I_F = 60 \text{ mA}$, $T_a = 25^\circ\text{C}$)

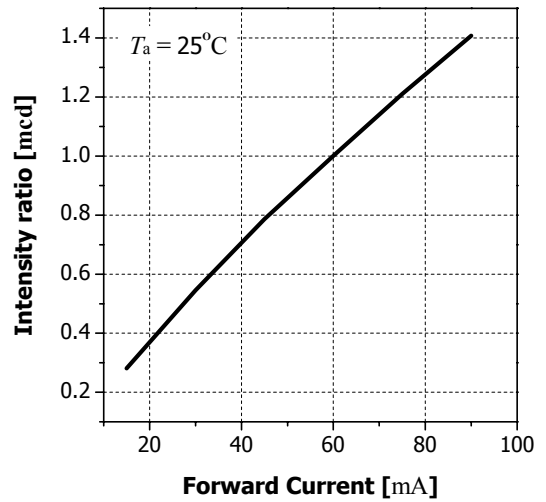
b		e		f	
x	y	x	y	x	y
0.264	0.267	0.296	0.276	0.311	0.294
0.280	0.248	0.311	0.294	0.330	0.318
0.296	0.276	0.307	0.315	0.330	0.339
0.287	0.295	0.287	0.295	0.307	0.315

6. Characteristic Diagram

Forward Current vs. Forward Voltage

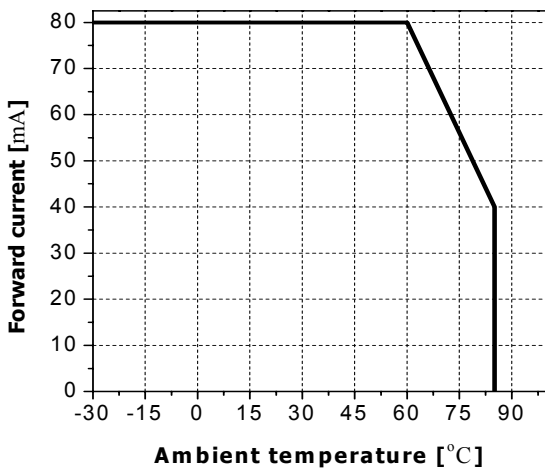


Intensity vs. Forward Current

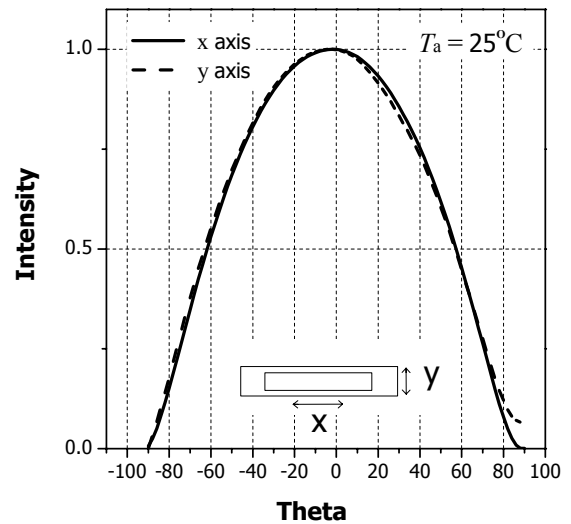


Forward Current vs. Ambient Temperature

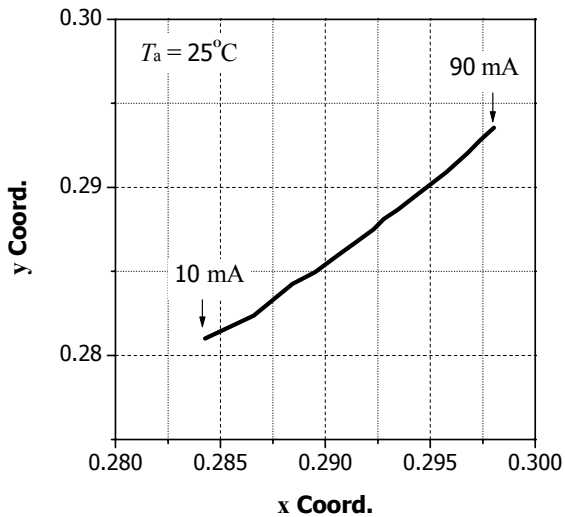
(Tj max = 125 °C)



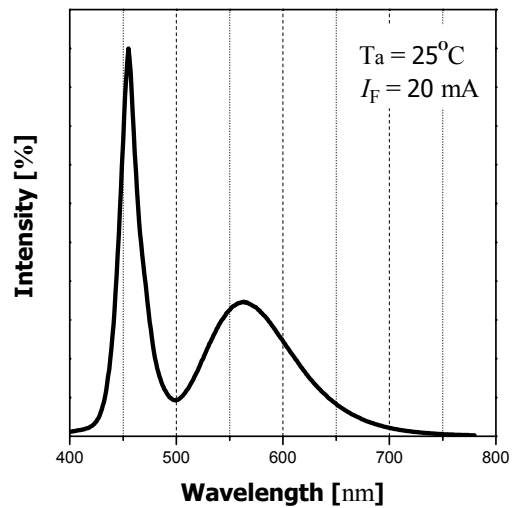
Radiation Diagram



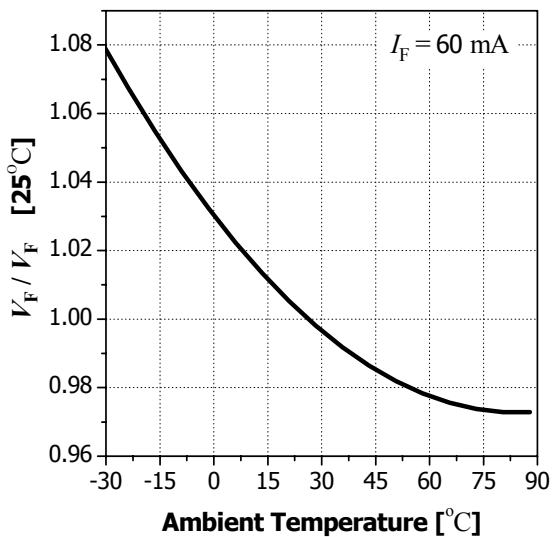
Color Coordinate vs. Forward Current



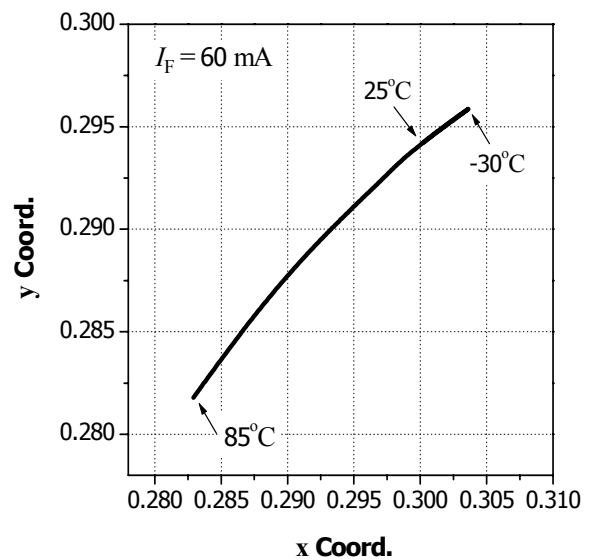
Spectrum



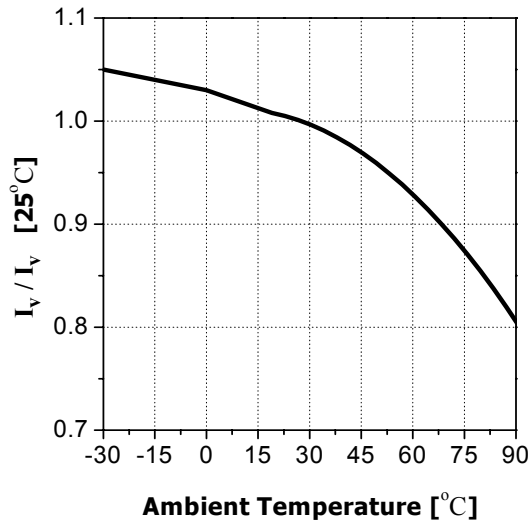
Forward Voltage vs. Ambient Temperature



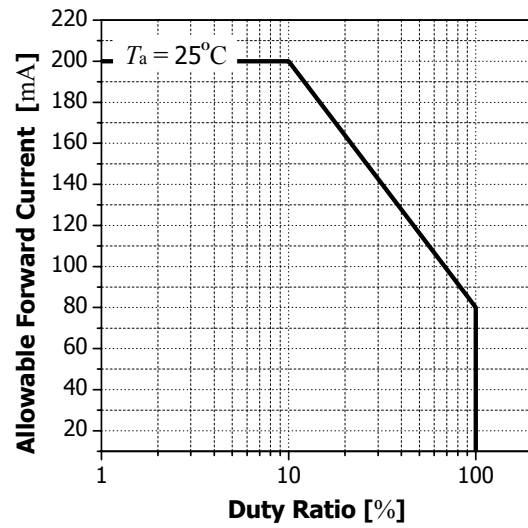
Color Coordinate vs. Ambient Temperature



Relative Luminosity vs. Ambient Temperature



Allowable Forward Current vs. Duty Ratio



* Pulse width $T_w \leq 0.1\text{ms}$

7. Reliability

(1) TEST ITEMS AND RESULTS

TEST ITEM	Test conditions	Note	Number of Damaged	Reference
Life Test 1	$T_a = 25^\circ\text{C}; I_F = 80 \text{ mA}$	1,000 hr	0/20	EIAJ ED-4701 100 101
High Humidity Heat Life Test	$T_a = 60^\circ\text{C}; RH = 90\%, I_F = 60 \text{ mA}$	1,000 hr		EIAJ ED-4701 100 102
Thermal Shock	$-30^\circ\text{C} \sim 85^\circ\text{C}$ (30 min) (30 min)	20 cycle	0/50	EIAJ ED-4701 300 307
High Temperature Life Test* ¹	$T_a = 85^\circ\text{C}; I_F = 60\text{mA}$	1,000 hr	0/20	-
Low Temperature Life Test	$T_a = -40^\circ\text{C}; I_F = 80 \text{ mA}$	1,000 hr	0/20	-
High Temperature Storage	$T_a = 100^\circ\text{C}$	1,000 hr	0/50	EIAJ ED-4701 200 201
Low Temperature Storage	$T_a = -40^\circ\text{C}$	1,000 hr	0/50	EIAJ ED-4701 200 202
Humidity Heat Storage	$T_a = 60^\circ\text{C}; RH = 90\%$	1,000 hr	0/20	
ESD	Human Body Mode : 1 kV	1 time	0/50	MIL-STD 888E

*¹ TEST CONDITION : PCB (Material : FR-4, Thickness : 1.6T)

-Operating Condition : $R\Theta = 140 \text{ }^\circ\text{C/W}$.

(2) CRITERIA FOR JUDGING THE DAMAGE

Item	Symbol	Test Condition	Criteria for Judgment	
			Min.	Max.
Forward Voltage	V_F	$I_F = 60 \text{ mA}$	-	U.S.L \times 1.2
Reverse Current	I_R	$V_R = 5 \text{ V}$	-	U.S.L \times 2.0
Luminous Intensity	I_V	$I_F = 60 \text{ mA}$	L.S.L \times 0.7	-

U.S.L. : Upper Standard Level, L.S.L. : Lower Standard Level

8. Precautions

(1) Storage conditions

- Keep the product in a dry box or a desiccator with a desiccant in order to prevent moisture absorption.
 - a. Keep it at a temperature in the range from 5°C to 30°C and at a humidity of less than 60% RH.
- In case of being stored for more than 3 months, the product should be sealed with Nitrogen gas.

(2) After opening the package

- When soldering, this could result in a decrease of the photoelectric effect or light intensity.
 - a. Soldering should be done right after mounting the product.
 - b. Keep the temperature in the range from 5°C to 40°C and the humidity at less than 30%.

- Soldering should be done within 7 days after opening the desiccant package.

If the product has been exposed for more than 7 days after opening the package or the indicating color of the desiccator changes, the product must be baked at a temperature between 60°C and 65°C for 10 to 12 hours.

- An unused and unsealed product should be repacked in a desiccant package and kept sealed in a dry atmosphere.

(3) Precautions for use

- Any external mechanical force or excessive vibration should not be applied to the product during cooling after soldering, and it is preferable to avoid rapid cooling.
- The product should not be mounted on a distorted part of PCB.
- Gloves or wrist bands for ESD(Electric Static Discharge) should be wore in order to prevent ESD and surge damage, and all devices and equipments must be grounded to the earth.

(4) Miscellaneous

- Radiation resistance is not considered.
- When cleaning the product, any kind of fluid such as water, oil and organic solvent must not be used and IPA(Isopropyl Alcohol) must be used.
- When using the product, operating current should be settled in consideration of the maximum ambient temperature.
- Its appearance or specification for improvement is subject to change without notice.

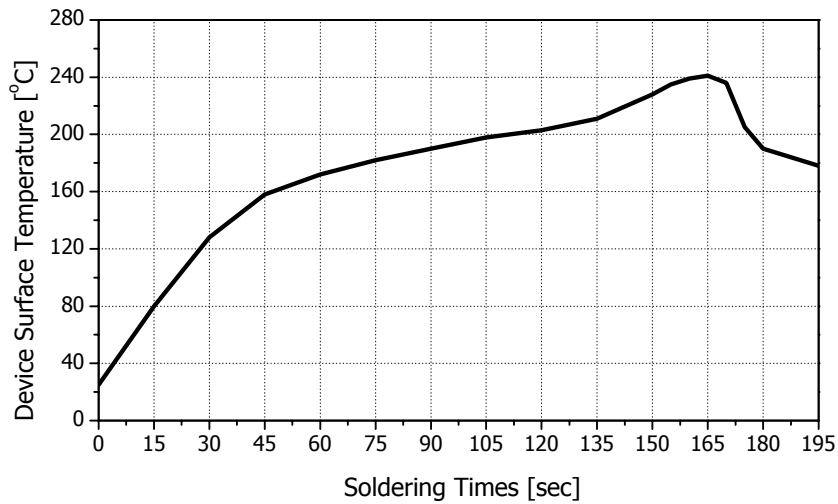
9. Soldering Profile

The LED can be soldered in place using the reflow soldering method.

(1) Lead solder

Preliminary heating to be at maximum 210°C for maximum 2 minutes.

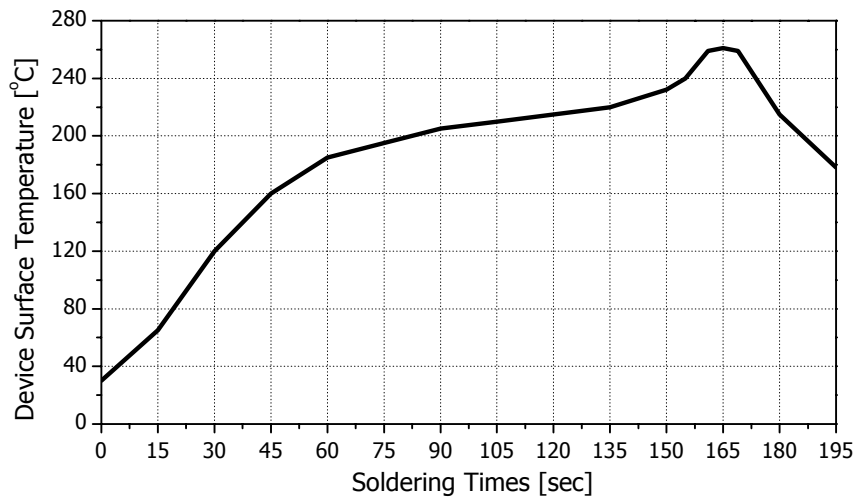
Soldering heat to be at maximum 240°C for maximum 10 seconds.



(2) Lead-free solder

Preliminary heating to be at maximum 220°C for maximum 2 minutes.

Soldering heat to be at maximum 260°C for maximum 10 seconds.

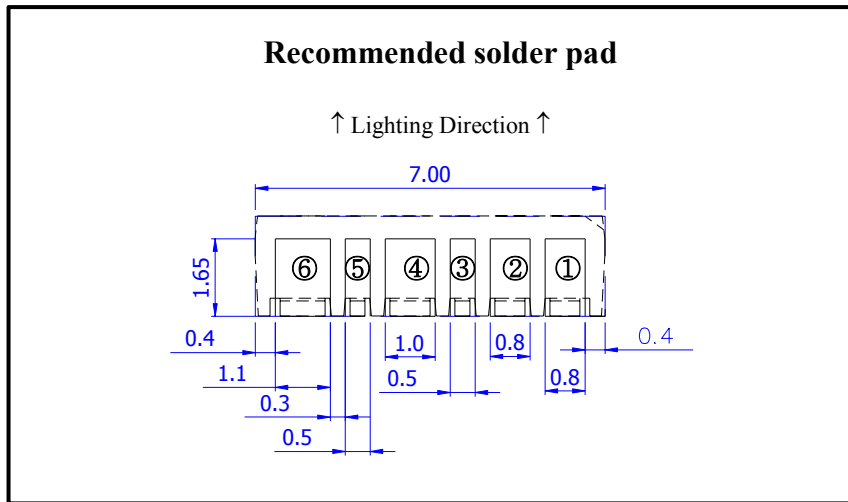
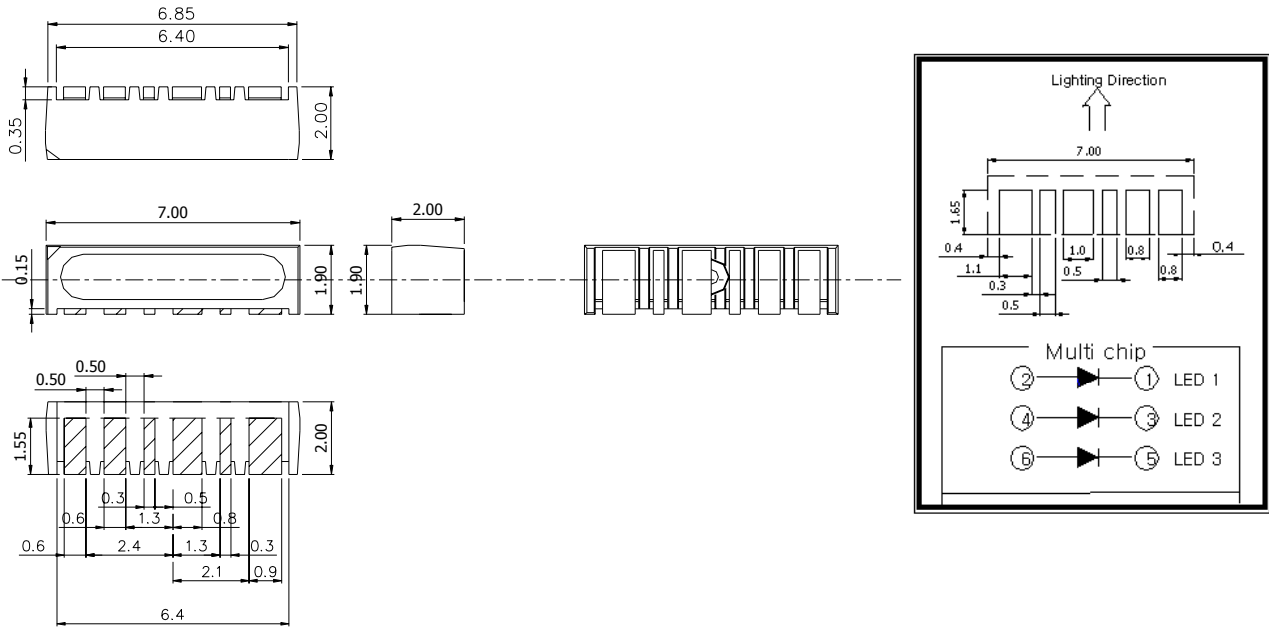


(3) Hand Soldering conditions

Not more than 5 seconds @MAX 300°C, under Soldering iron.

10. Outline Dimension

(Tolerance : ± 0.2 , Unit : mm)



13. History

Rev. No.	Contents	Date
1.00	- The institution of New Spec.	2008. 06. 03

Published by
SEOUL SEMICONDUCTOR CO., LTD.
<http://www.seoulsemicon.com>
148-29, Gasan-Dong, Geumcheon-Gu,
Seoul, 153-801. South Korea
© All Right Reserved.